

### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
60V	$6\Omega$ @ $V_{GS} = 5V$	200mA

### **Description**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Motor Control
- Power Management Functions

### **Features and Benefits**

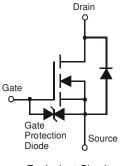
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1.2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The 2N7002AQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

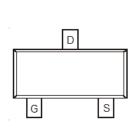
https://www.diodes.com/quality/product-definitions/

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
  Leadframe. Solderable per MIL-STD-202. Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)







Equivalent Circuit

Top View Pin-Out

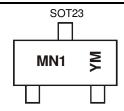
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
2N7002AQ-7	SOT23	3,000/Tape & Reel
2N7002AQ-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



MN1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Bate Code Noy												
Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	C		Н		J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	60	V		
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$ $T_A = +100^{\circ}C$	l <sub>D</sub>	180 130 115	mA
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady State			Ι <sub>D</sub>	220 160 140	mA
Maximum Continuous Body Diode Forward Current	ls	0.5	Α		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	)		I <sub>DM</sub>	800	mA

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	D-	370	mW	
Total Fower Dissipation	(Note 6)	$P_{D}$	540	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	Dov	348		
Thermal nesistance, Junction to Ambient	(Note 6)	Reja	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R <sub>0</sub> JC	91		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

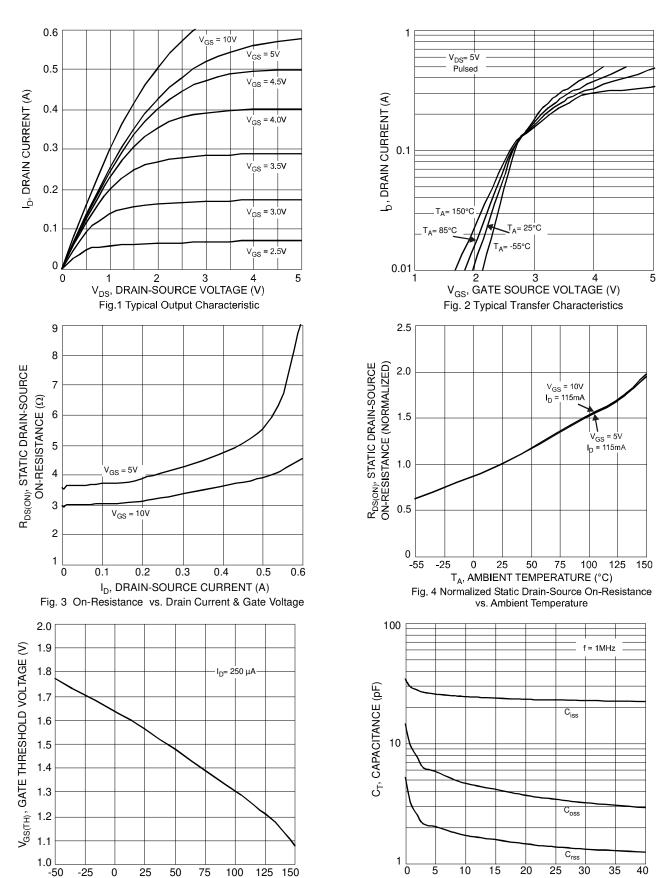
## **Electrical Characteristics** (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	- <b>,</b>		- 71				
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T <sub>C</sub> = +25°C @ T <sub>C</sub> = +125°C	IDSS	_	_	1.0 500	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage		Igss	_	_	±10	μΑ	V <sub>G</sub> S = ±20V, V <sub>D</sub> S = 0V
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		VGS(th)	1.2	_	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
Static Drain-Source On-Resistance	@ T <sub>J</sub> = +25°C	D		3.5	6		V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 0.115A
	@ T <sub>J</sub> = +125°C	RDS(ON)	_	3.0	5	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.115A
Forward Transconductance	orward Transconductance		80	_	_	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.115A
DYNAMIC CHARACTERISTICS (Note	: 8)						
nput Capacitance		Ciss	_	23	_	pF	
Output Capacitance		Coss	_	3.4	_	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	Reverse Transfer Capacitance		_	1.4	_	pF	
Gate Resistance	Gate Resistance		_	260	400	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (No	ote 8)				•		
Turn-On Delay Time		td(ON)	_	10	_	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.115A, R <sub>L</sub> = 150
Turn-Off Delay Time		tD(OFF)	_	33	_	ns	$\Omega$ , V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25 $\Omega$

Notes:

- Device mounted on FR-4 PCB, with minimum recommended pad layout.
  Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to product testing.





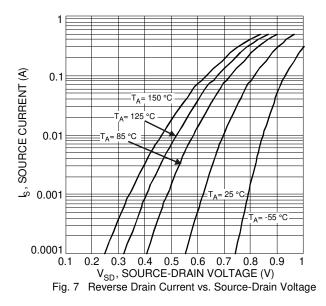
 $T_A$ , AMBIENT TEMPERATURE (°C)

Fig. 5 Gate Threshold Variation vs. Ambient Temperature

V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

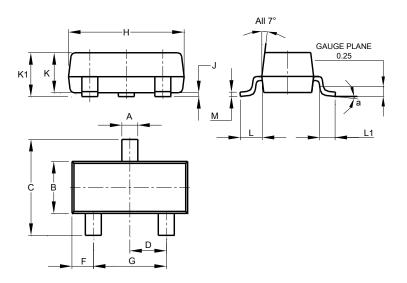
Fig. 6 Typical Total Capacitance





# **Package Outline Dimensions**

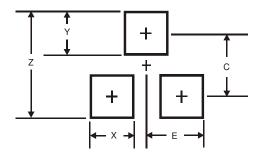
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	8°						
All	Dimens	ions in	mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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